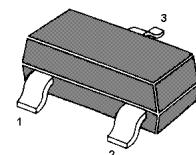


BCV27 / BCV47

NPN Darlington Transistors

for preamplifier input applications



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Collector Base Voltage BCV27 BCV47		V_{CBO}	40	V
			80	
Collector Emitter Voltage BCV27 BCV47		V_{CEO}	30	V
			60	
Emitter Base Voltage		V_{EBO}	10	V
Collector Current		I_C	500	mA
Peak Collector Current		I_{CM}	800	mA
Base Current		I_B	100	mA
Total Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5 \text{ V}$, $I_C = 1 \text{ mA}$ at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$ at $V_{CE} = 5 \text{ V}$, $I_C = 100 \text{ mA}$	BCV27	h_{FE}	4000	-	-	-
	BCV47	h_{FE}	2000	-	-	-
	BCV27	h_{FE}	10000	-	-	-
	BCV47	h_{FE}	4000	-	-	-
	BCV27	h_{FE}	20000	-	-	-
	BCV47	h_{FE}	10000	-	-	-
Collector Base Cutoff Current at $V_{CB} = 30 \text{ V}$ at $V_{CB} = 60 \text{ V}$	BCV27	I_{CBO}	-	-	100	nA
	BCV47	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 10 \text{ V}$		I_{EBO}	-	-	100	nA
		I_{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100 \mu\text{A}$	BCV27	$V_{(BR)CBO}$	40	-	-	-
	BCV47	$V_{(BR)CBO}$	80	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 10 \text{ mA}$	BCV27	$V_{(BR)CEO}$	30	-	-	-
	BCV47	$V_{(BR)CEO}$	60	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10 \mu\text{A}$		$V_{(BR)EBO}$	10	-	-	V
		$V_{(BR)EBO}$	10	-	-	V
Collector Emitter Saturation Voltage at $I_C = 100 \text{ mA}$, $I_B = 0.1 \text{ mA}$		$V_{CE(sat)}$	-	-	1	V
		$V_{CE(sat)}$	-	-	1	V
Base Emitter Saturation Voltage at $I_C = 100 \text{ mA}$, $I_B = 0.1 \text{ mA}$		$V_{BE(sat)}$	-	-	1.5	V
		$V_{BE(sat)}$	-	-	1.5	V
Base Emitter On-state Voltage at $I_C = 10 \text{ mA}$, $V_{CE} = 5 \text{ V}$		$V_{BE(on)}$	-	-	1.4	V
		$V_{BE(on)}$	-	-	1.4	V
Transition Frequency at $V_{CE} = 5 \text{ V}$, $I_C = 30 \text{ mA}$, $f = 100 \text{ MHz}$		f_T	-	220	-	MHz



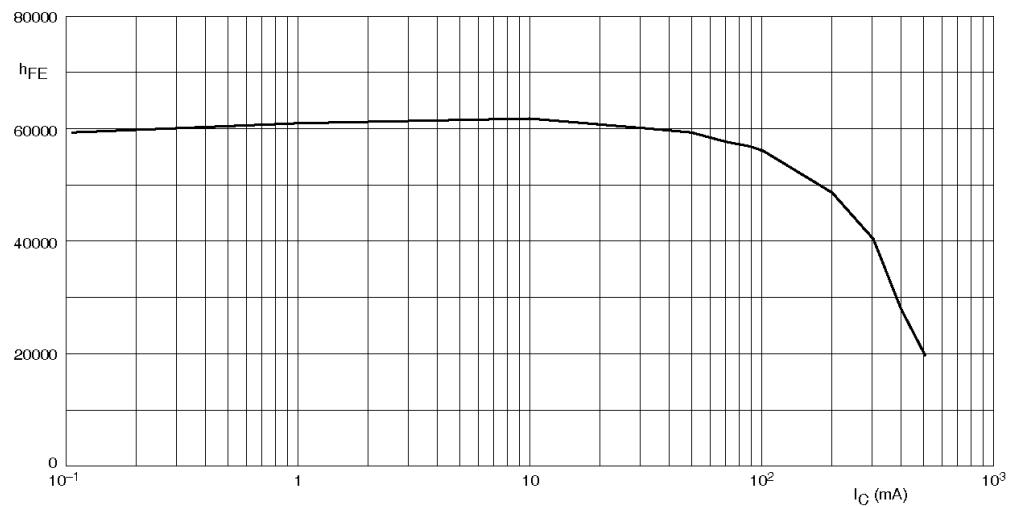
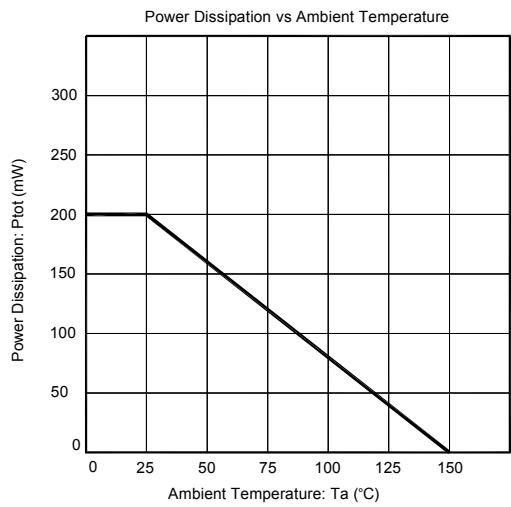
TOP DYNAMIC

ISO14001 : 2004 ISO 9001 : 2008 OHSAS 18001 : 2007 IECQ QC 080000

Certificate No. 12150507 Certificate No. 50114012 Certificate No. 0513150006

Code No. ESD/HQ/001/NR2 Code No. ESD/HQ/001/NR2

Dated : 18/08/2012



$V_{CE} = 2$ V.

DC current gain; typical values.

TOP DYNAMIC



Dated : 18/08/2012